



HM4033

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The HM4033 is designed for high current general purpose amplifier applications.

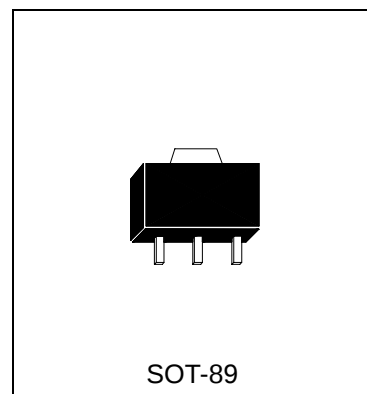
Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation ($T_A=25^{\circ}\text{C}$) 1 W
- Maximum Voltages and Currents ($T_A=25^{\circ}\text{C}$)
 V_{CBO} Collector to Base Voltage -80 V
 V_{CEO} Collector to Emitter Voltage -80 V
 V_{EBO} Emitter to Base Voltage -5 V
 I_C Collector Current -1 A

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-80	-	-	V	$I_C=-10\mu\text{A}$, $I_E=0$
BV_{CEO}	-80	-	-	V	$I_C=-10\text{mA}$, $I_B=0$
BV_{EBO}	-5	-	-	V	$I_C=-10\mu\text{A}$, $I_C=0$
I_{CBO}	-	-	-100	nA	$V_{CB}=-60\text{V}$, $I_E=0$
I_{EBO}	-	-	-100	nA	$V_{EB}=-5\text{V}$, $I_C=0$
$*V_{CE(sat)1}$	-	-	-150	mV	$I_C=-150\text{mA}$, $I_B=-15\text{mA}$
$*V_{CE(sat)2}$	-	-	-500	mV	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$
$*V_{BE(sat)1}$	-	-	-900	mV	$I_C=-150\text{mA}$, $I_B=-15\text{mA}$
$*V_{BE(sat)2}$	-	-	-1.1	V	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$
$*h_{FE1}$	75	-	-		$V_{CE}=-5\text{V}$, $I_C=-0.1\text{mA}$
$*h_{FE2}$	100	-	-		$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$
$*h_{FE3}$	70	-	-		$V_{CE}=-5\text{V}$, $I_C=-500\text{mA}$
$*h_{FE4}$	25	-	-		$V_{CE}=-5\text{V}$, $I_C=-1\text{A}$
f_T	100	-	-	MHz	$V_{CE}=-10\text{V}$, $I_C=-50\text{mA}$, $f=100\text{MHz}$
Cob	-	-	20	pF	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$

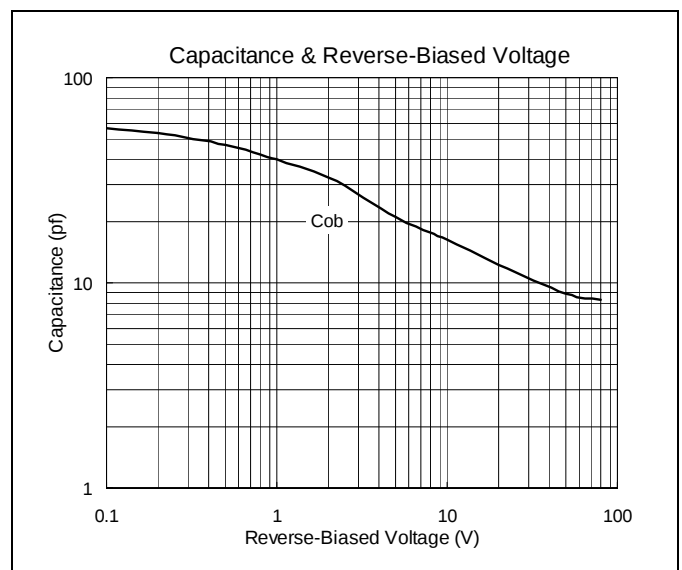
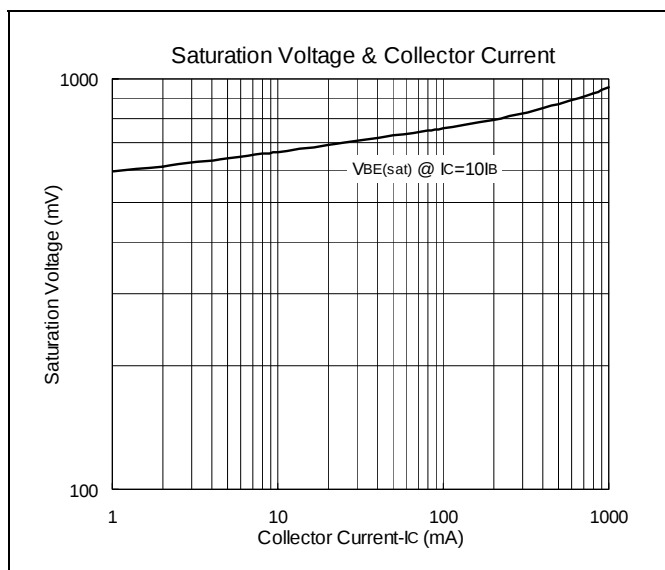
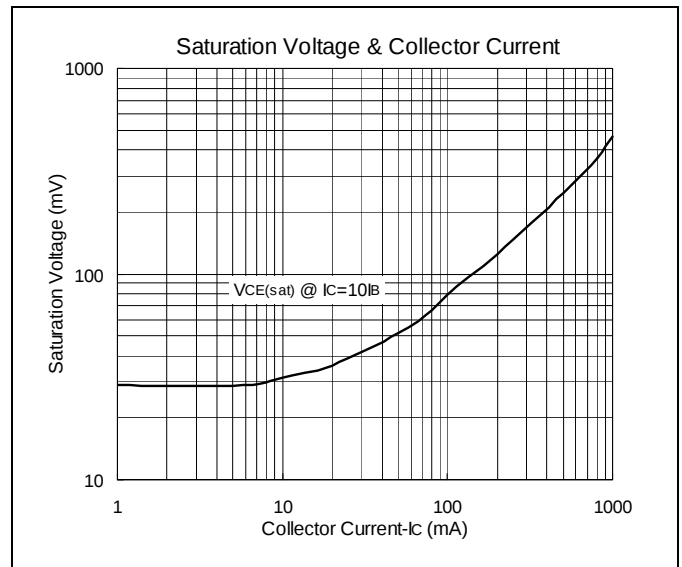
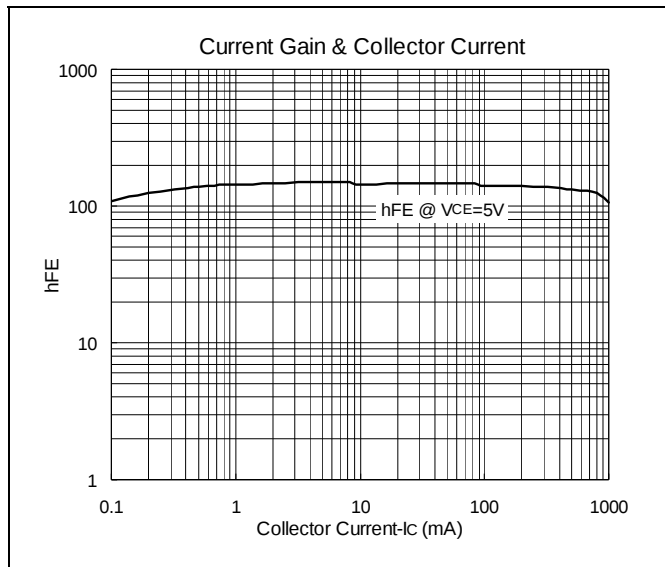
*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$



SOT-89

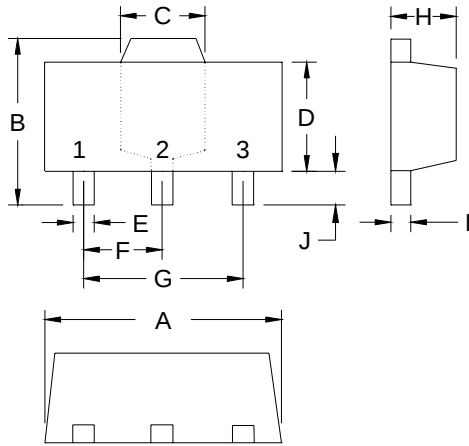


Characteristics Curve



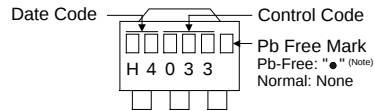


SOT-89 Dimension



3-Lead SOT-89 Plastic
Surface Mounted Package
HSMC Package Code: M

Marking:



Note: Green label is used for pb-free packing

Pin Style: 1.Base 2.Collector 3.Emitter

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.40	4.60
B	4.05	4.25
C	1.50	1.70
D	2.40	2.60
E	0.36	0.51
F	*1.50	-
G	*3.00	-
H	1.40	1.60
I	0.35	0.41

*: Typical, Unit: mm

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Head Office And Factory:

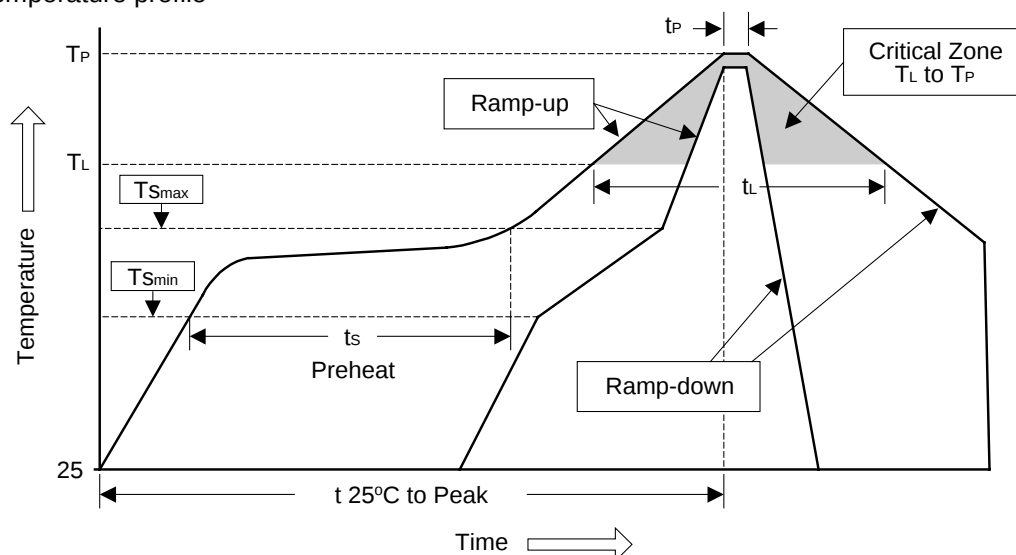
- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931



Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec